Takeshi Kanashima

List of Publications by Year
in descending order

92	980	516710 16	526287 27
papers	citations	h-index	g-index

92	92	92	830
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Electrical properties of pseudo-single-crystalline Ge films grown by Au-induced layer exchange crystallization at 250â€‰Â°C. Journal of Applied Physics, 2018, 123, 215704.	2.5	24
2	Robust spin-current injection in lateral spin valves with two-terminal Co2FeSi spin injectors. AIP Advances, 2017, 7, 055808.	1.3	2
3	A crystalline germanium flexible thin-film transistor. Applied Physics Letters, 2017, 111, .	3.3	20
4	Exchange coupling in metallic multilayers with a top FeRh layer. AIP Advances, 2016, 6, .	1.3	4
5	Spin transport in p-Ge through a vertically stacked Ge/Fe3Si junction. Applied Physics Letters, 2016, 109, .	3.3	23
6	All-epitaxial Co2FeSi/Ge/Co2FeSi trilayers fabricated by Sn-induced low-temperature epitaxy. Journal of Applied Physics, 2016, 119, .	2.5	17
7	A low-temperature fabricated gate-stack structure for Ge-based MOSFET with ferromagnetic epitaxial Heusler-alloy/Ge electrodes. Japanese Journal of Applied Physics, 2016, 55, 063001.	1.5	3
8	P(VDF-TeFE)/Organic Semiconductor Structure Ferroelectric-Gate FETs. Topics in Applied Physics, 2016, , 187-201.	0.8	0
9	Low-temperature<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>B</mml:mi><mml:mn>2</mml:mn></mml:mrow></mml:m and magnetic properties of<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>Fe</mml:mi><mml:mrow><mml:mn>100- on bcc alloys. Physical Review B, 2015, 92, .	3.2	8
10	Effect of atomic-arrangement matching on La2O3/Ge heterostructures for epitaxial high-k-gate-stacks. Journal of Applied Physics, 2015, 118, .	2.5	6
11	A pseudo-single-crystalline germanium film for flexible electronics. Applied Physics Letters, 2015, 106, .	3.3	44
12	Spin-related thermoelectric conversion in lateral spin-valve devices with single-crystalline Co₂FeSi electrodes. Applied Physics Express, 2015, 8, 043003.	2.4	12
13	Air damping effect on the air-based CMUT operation. Journal of the Korean Physical Society, 2015, 67, 486-495.	0.7	0
14	Columnar Growth of BiFeO₃Films Prepared by Magnetic-field-assisted Pulsed Laser Deposition. Ferroelectrics, 2014, 466, 63-73.	0.6	4
15	Current conduction in single-domain BiFeO₃thin films. Japanese Journal of Applied Physics, 2014, 53, 08NA01.	1.5	2
16	Texture measurement and identification of object surface by MEMS tactile sensor. , 2014, , .		4
17	Multimodal measurement of proximity and touch force by light- and strain-sensitive multifunctional MEMS sensor. , 2014, , .		15
18	Organic ferroelectric gate field-effect transistor memory using high-mobility rubrene thin film. Japanese Journal of Applied Physics, 2014, 53, 04ED11.	1.5	17

#	Article	IF	Citations
19	Proximity and Tactile Sensing Using a Single MEMS Sensor with Photo- and Strain Sensitivities. IEEJ Transactions on Sensors and Micromachines, 2014, 134, 229-234.	0.1	11
20	Active Touch Sensing by Multi-axial Force Measurement Using High-Resolution Tactile Sensor with Microcantilevers. IEEJ Transactions on Sensors and Micromachines, 2014, 134, 58-63.	0.1	16
21	Preparation of epitaxial BiFeO3 thin films on La-SrTiO3 substrate by using magnetic-field-assisted pulsed laser deposition. Journal of the Korean Physical Society, 2013, 62, 1041-1045.	0.7	5
22	Identification of various kinds of papers using multi-axial tactile sensor with micro-cantilevers. , 2013, , .		6
23	Force intensity and direction measurement in real time using miniature tactile sensor withl microcantilevers embedded in PDMS. , 2013, , .		1
24	Fabrication and Noise Reduction of the Miniature Tactile Sensor Using Through-Silicon-Via Connection with Signal Amplifier. Japanese Journal of Applied Physics, 2013, 52, 06GL08.	1.5	10
25	Multi-axial tactile sensor with micro-cantilever embedded in hemispherical elastomer for surface texture measurement. , 2013, , .		3
26	Repetition Rate Dependence of Ferroelectric Properties of Polycrystalline BiFeO₃Films Prepared by Pulsed Laser Deposition Method. Ferroelectrics, 2013, 453, 1-7.	0.6	4
27	Review of Texture Measurement of Object Surface by Tactile Sensor with Inclined Micro-cantilevers. IEEJ Transactions on Sensors and Micromachines, 2013, 133, 147-154.	0.1	5
28	Heterogeneous Integration of LSI Amplifier and the Tactile Sensor Using Stacking and Through-Si-Via Techniques. Materials Research Society Symposia Proceedings, 2012, 1427, 14.	0.1	1
29	Ferroelectric and Piezoelectric Properties of Polycrystalline BiFeO₃ Thin Films Prepared by Pulsed Laser Deposition under Magnetic Field. Japanese Journal of Applied Physics, 2012, 51, 09MD05.	1.5	10
30	Organic Ferroelectric Field-Effect Transistor Memory Using Flat Poly(vinylidene) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 307 Td (fluorideâ€ 02BK06.	1.5	6
31	Passivation of Ge(100) and (111) Surfaces by Termination of Nonmetal Elements. Japanese Journal of Applied Physics, 2012, 51, 04DA06.	1.5	1
32	Tactile sensor array using microcantilever with nickelâ€“chromium alloy thin film of low temperature coefficient of resistance and its application to slippage detection. Sensors and Actuators A: Physical, 2012, 186, 32-37.	4.1	69
33	Miniature Ultrasonic and Tactile Sensors for Dexterous Robot. Transactions on Electrical and Electronic Materials, 2012, 13, 215-220.	1.9	4
34	Mutiferroic Properties of Polycrystalline Sr-Substituted BiFeO₃Thin Films Prepared by Pulsed Laser Deposition. Ferroelectrics, 2011, 416, 119-124.	0.6	3
35	Fabrication of tactile sensor array using microcantilever with low-TCR nickel-chromium alloy thin film for slippage detection. Procedia Engineering, 2011, 25, 627-630.	1.2	2
36	Influences of perforation ratio in characteristics of capacitive micromachined ultrasonic transducers in air. Sensors and Actuators A: Physical, 2011, 171, 191-198.	4.1	8

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37	Characterization of epitaxial BiFeO3 thin films prepared by ion beam sputtering. Current Applied Physics, 2011, 11, S244-S246.	2.4	8
38	Multiferroic properties of polycrystalline Zn-substituted BiFeO3 thin films prepared by pulsed laser deposition. Current Applied Physics, 2011, 11, S270-S273.	2.4	10
39	Improvement in the Property of Field Effect Transistor Having the HfO2/Ge Structure Fabricated by Photoassisted Metal Organic Chemical Vapor Deposition with Fluorine Treatment. Japanese Journal of Applied Physics, 2011, 50, 04DA11.	1.5	3
40	Fabrication of a Flexible Array for Tactile Sensors with Microcantilevers and the Measurement of the Distribution of Normal and Shear Forces. Japanese Journal of Applied Physics, 2011, 50, 06GM02.	1.5	5
41	Crosstalk Reduction of Tactile Sensor Array with Projected Cylindrical Elastomer over Sensing Element. Japanese Journal of Applied Physics, 2011, 50, 06GM08.	1.5	11
42	Preparation of BiFeO$_{3}$ Thin Films on SrRuO$_{3}$/SrTiO$_{3}$(001) Substrate by Dual Ion Beam Sputtering. Japanese Journal of Applied Physics, 2011, 50, 09NB01.	1.5	12
43	Preparation of BiFe_{0.9}Co_{0.1}O₃ Films by Pulsed Laser Deposition under Magnetic Field. Japanese Journal of Applied Physics, 2011, 50, 09NB03.	1.5	10
44	Growth of high quality BiFeO<inf>3</inf> thin films by dual ion beam sputtering. , 2011, , .		2
45	Structural and Ferroelectric Properties of Large c/a Phase Bismuth Ferrite Thin Films Prepared by Ion Beam Sputtering. Materials Research Society Symposia Proceedings, 2011, 1292, 3.	0.1	0
46	Improvement in the Electrical Characteristics of a Fluorinated HfO2/Ge Gate Stack by Using a Nitrogen Radical Treatment. Journal of the Korean Physical Society, 2011, 59, 2503-2508.	0.7	1
47	Preparation and Characterization of BiFeO3 Thin Film Deposited on ITO Substrate by Using Pulsed Laser Deposition. Journal of the Korean Physical Society, 2011, 59, 2537-2541.	0.7	5
48	X-ray Diffraction Study of Electric-field-induced Strains in Polycrystalline BiFeO3 Thin Films at Low Temperature Using Synchrotron Radiation. Journal of the Korean Physical Society, 2011, 59, 2556-2559.	0.7	4
49	Theoretical analysis of fluorine-passivated germanium surface for high-k/Ge gate stack by molecular orbital method. Applied Surface Science, 2010, 257, 917-920.	6.1	7
50	Characterization of Interface States of HfO2/Ge with Fluorine Treatment by Using DLTS/ICTS. ECS Transactions, 2010, 33, 235-241.	0.5	1
51	Structural and ferroelectric properties of epitaxial Bi5Ti3FeO15 and natural-superlattice-structured Bi4Ti3O12â€“Bi5Ti3FeO15 thin films. Journal of Applied Physics, 2010, 108, .	2.5	42
52	Ferroelectric Properties of Bi_{1.1}Fe_{1-x}Co_xO₃ Thin Films Prepared by Chemical Solution Deposition Using Iterative Rapid Thermal Annealing in N₂ and O₂. Japanese Journal of Applied Physics, 2010, 49, 09MB05.	1.5	14
53	Fabrication and Characterization of Ferroelectric Poly(vinylidene fluorideâ€“tetrafluoroethylene) Gate Field-Effect Transistor Memories. Japanese Journal of Applied Physics, 2010, 49, 04DD14.	1.5	15
54	Leakage Current Reduction and Ferroelectric Property of BiFe_{1-x}Co_xO₃ Thin Films Prepared by Chemical Solution Deposition Using Iterative Rapid Thermal Annealing at Approximately 520 Â°C. Japanese Journal of Applied Physics, 2010, 49, 095803.	1.5	7

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55	ï¼“æ–¹å•ã,«ãƒ³ãƒ•ã¤ãƒ¬ãƒ¼ã,'ç"¨ã„ãŸåšè»¸è§¦è¦šã,»ãƒ³ã,µã®ä½œè£½ã•ãŸçŽç‰¹æ€§. IEEJ Transactions on Sensors and Micromachines	0.1	17
56	Stability Improvement of Tactile Sensor of Normal and Shear Stresses Using Ni-Cr Thin Film Gauge. IEEJ Transactions on Sensors and Micromachines, 2009, 129, 411-416.	0.1	22
57	Synergistic information encoding by combinatorial pulse operation of ferroelectrics. Applied Physics Letters, 2009, 95, 202905.	3.3	4
58	Fixed-Oxide-Charge Characterization by Photoreflec-tance Spectroscopy in HfO2 on Ge treated by Fluorine. ECS Transactions, 2009, 16, 699-705.	0.5	0
59	Pulsed Laser Deposition and Characterization of Sr and Zn Co-Substituted BiFeO₃Thin Films. Japanese Journal of Applied Physics, 2009, 48, 09KB03.	1.5	27
60	Ferroelectric and structural properties of stress-constrained and stress-relaxed polycrystalline BiFeO3 thin films. Journal of Applied Physics, 2009, 105, 061617.	2.5	20
61	Tactle array sensor with inclined chromium/silicon piezoresistive cantilevers embedded in elastomer. , 2009, , .		18
62	Characteristics improvement of HfO2/Ge gate stack structure by fluorine treatment of germanium surface. Applied Surface Science, 2008, 254, 6932-6936.	6.1	10
63	ENHANCEMENT OF MEMORY RETENTION TIME OF MFIS STRUCTURE WITH SBT FERROELECTRIC AND SiO₂ BUFFER LAYERS TREATED BY NITROGEN RADICAL IRRADIATION. Integrated Ferroelectrics, 2008, 96, 27-39.	0.7	5
64	PREPARATION AND CHARACTERIZATION OF HAFNIUM SILICATE DIELECTRIC LAYERS BY PHOTO-ASSISTED MOCVD USING MIXED PRECURSOR OF Hf(O-t-C₄H₉)₄ AND Si(O-t-C₄H₉)₄. Integrated Ferroelectrics, 2008, 97, 103-110.	0.7	2
65	Microwave Tunable Devices Composed of Coplanar Waveguide Line with (Ba0.6,Sr0.4)TiO3/Au/Cr/(Ba0.6,Sr0.4)TiO3Sandwich Structure. Japanese Journal of Applied Physics, 2008, 47, 7500-7504.	1.5	3
66	X-ray diffraction study of polycrystalline BiFeO3 thin films under electric field. Applied Physics Letters, 2008, 93, 042907.	3.3	6
67	Fabrication and Normal/Shear Stress Responses of Tactile Sensors of Polymer/Si Cantilevers Embedded in PDMS and Urethane Gel Elastomers. IEEJ Transactions on Sensors and Micromachines, 2008, 128, 193-197.	0.1	20
68	Development of a Microscopic Three-Axis Tactile Sensor: Preliminary Examinations to Establish Sensing Algorithm by Using a Simulated Mockup. Lecture Notes in Computer Science, 2008, , 561-566.	1.3	4
69	FERROELECTRIC GATE FET MEMORY BASED ON CONDUCTION OF FERROELECTRIC-INSULATOR INTERFACE. Integrated Ferroelectrics, 2007, 89, 160-170.	0.7	2
70	Fabrication and Characterization of Silicon-Polymer Beam Structures for Cantilever-Type Tactile Sensors. , 2007, , .		10
71	Data retention time of MFIS-FET memory structure improved with nitrogen and oxygen radical irradiation treatment. , 2006, , .		0
72	Preparation and characterization of HfO2thin films by photo-assisted MOCVD. European Physical Journal Special Topics, 2006, 132, 279-283.	0.2	3

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73	First-Principles Study of Tetragonality Ratio and Unit-Cell Volume Influence on Spontaneous Polarization of BaTiO3 and PbTiO3. Zairyo/Journal of the Society of Materials Science, Japan, 2006, 55, 169-172.	0.2	3
74	Preparation of fluorocarbon thin film deposited by soft X-ray ablation and its electrical characteristics and thermal stability. Applied Surface Science, 2006, 252, 7774-7780.	6.1	6
75	Enhancement of electrical properties in polycrystalline BiFeO3 thin films. Applied Physics Letters, 2006, 89, 192902.	3.3	157
76	Fabrication and Characterization of Ferroelectric Gate Field-Effect Transistor Memory Based on Ferroelectricâ€“Insulator Interface Conduction. Japanese Journal of Applied Physics, 2006, 45, 8608-8610.	1.5	12
77	IMPROVEMENT OF MEMORY RETENTION IN METAL-FERROELECTRIC-INSULATOR-SEMICONDUCTOR STRUCTURE BY SrBi2Ta2O9 SURFACE MODIFICATION INDUCED BY NITROGEN AND OXYGEN RADICAL IRRADIATION. Integrated Ferroelectrics, 2006, 84, 179-188.	0.7	6
78	A Trial of Smell Discrimination by SnO2 Gas Sensor. Zairyo/Journal of the Society of Materials Science, Japan, 2006, 55, 165-168.	0.2	3
79	Contactless Characterization of Fixed Charges in HfO2Thin Film from Photoreflectance. Japanese Journal of Applied Physics, 2005, 44, 2409-2414.	1.5	3
80	Characterization of Ferroelectric Thin Film/SiO2/Si Structure by Photoreflectance. Ferroelectrics, 2004, 303, 119-123.	0.6	0
81	Basic characteristics of metal-ferroelectric-insulator-semiconductor structure using a high-k PrOx insulator layer. Journal of Applied Physics, 2003, 93, 4137-4143.	2.5	19
82	BURST REACTION OF THIN FILMS EXCITED BY HIGH-FLUX SOFT X-RAYS. Surface Review and Letters, 2002, 09, 401-405.	1.1	0
83	Microfocusing of soft X-ray undulator light using an elliptically bent cylinder mirror. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2001, 467-468, 287-290.	1.6	2
84	Nondestructive and Contactless Monitoring Technique of Si Surface Stress by Photoreflectance. Japanese Journal of Applied Physics, 2001, 40, 2844-2848.	1.5	11
85	Molecular orbital analysis of reaction processes of fluorine with H-terminated silicon (111) and (100) surfaces. Journal of Applied Physics, 1999, 85, 244-248.	2.5	3
86	Electronic characterization of Si/SiO2 structure using photo-CVD SiO2 thin film on atomically flat Si substrate. Applied Surface Science, 1998, 130-132, 214-220.	6.1	8
87	<title>Surface treatment effects on Si(111) and (100) surface structures and Si/SiO2 interface state</title>. , 1998, , .		0
88	Photoluminescence of SiO2 films grown by photo-induced chemical vapor deposition. Applied Surface Science, 1994, 79-80, 321-326.	6.1	23
89	Photoluminescence and Its Excimer Laser Irradiation Effects in SiO2Film Prepared by Photo-Induced Chemical Vapor Deposition. Japanese Journal of Applied Physics, 1993, 32, 3113-3119.	1.5	6
90	Optical characterizations of photoâ€induced chemical vapor deposition produced SiO2films in vacuum ultraviolet, ultraviolet, and visible region. Journal of Applied Physics, 1993, 74, 5742-5747.	2.5	15

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91	Preparation and characterization of ZrO/sub 2//Si structure. , 0, , .		0
92	Molecular orbital calculation of surface reaction of SnO/sub 2/ gas sensors for aminic and carboxylic smells. , 0, , .		3